Wuxi Unigroup Microelectronics Co.,Ltd

650V Super-junction Power MOSFET

Description

650V Super-junction Power MOSFET

Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs，designed according to the SJ principle. The Multi-EPI SJ MOSFET provide an extremely low switching, communication and conduction losses device with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler, designed by Wuxi Unigroup Microelectronics Company.

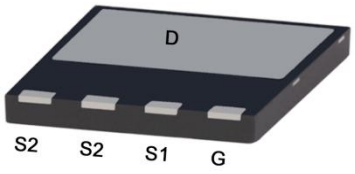
Features

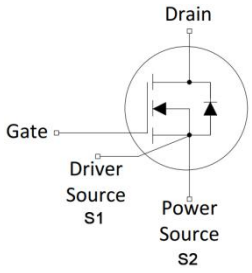
- Very low FOM RDS(on)×Qg
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger

DFN 8*8





Device Marking and Package Information

Device	Package	Marking
TPG65R365MH	DFN 8*8	65R365M

Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	700	V
$R_{DS(on),max}$	0.365	Ω
$Q_{g,typ}$	22	nC
I_D	11	A
$I_{D,pulse}$	33	A
E_{OSS} @ 400V	2.45	μJ
Body Diode di_F/dt	500	A/μs

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted				
Parameter		**Symbol**	**Value**	**Unit**
Continuous Drain Current	T_C = 25ºC	I_D	11	A
	T_C = 100ºC		6.6	
Pulsed Drain Current (note1)		$I_{D,pulse}$	33	A
Gate-Source Voltage		V_{GSS}	±30	V
Single Pulse Avalanche Energy (note2)		E_{AS}	215	mJ
Repetitive Avalanche Energy (note2)		E_{AR}	0.32	mJ
Avalanche Current		I_{AR}	1.8	A
MOSFET dv/dt Ruggedness, V_{DS} = 0...480V		dv/dt	50	V/ns
Power Dissipation For DFN 8*8		P_D	83	W
Continuous Diode Forward Current		I_S	9.4	A
Diode Pulsed Current (note1)		$I_{S,pulse}$	33	
Reverse Diode dv/dt (note3)		dv/dt	15	V/ns
Maximum Diode Commutation Speed (note3)		di_f/dt	500	A/μs
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+150	ºC

Thermal Resistance For DFN 8*8			
Parameter	**Symbol**	**Value**	**Unit**
Thermal Resistance, Junction-to-Case	R_{thJC}	1.5	ºC/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	

Electrical Characteristics T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 650V, V_{GS} = 0V, T_J = 25ºC	--	--	1	μA
		V_{DS} = 650V, V_{GS} = 0V, T_J = 150ºC	--	--	100	
Gate-Source Leakage Current	I_{GSS}	V_{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.5	--	4.5	V
Drain-Source On-State-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 5.5A	--	0.335	0.365	Ω
Gate Resistance	R_G	f = 1.0MHz open drain	--	18	--	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 100V, f = 1.0MHz	--	807	--	pF
Output Capacitance	C_{oss}		--	32	--	
Reverse Transfer Capacitance	C_{rss}		--	1.9	--	
Total Gate Charge	Q_g	V_{DD} = 520V, I_D = 11A, V_{GS} = 10V	--	22	--	nC
Gate-Source Charge	Q_{gs}		--	4	--	
Gate-Drain Charge	Q_{gd}		--	8	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 400V, I_D = 11A, R_G = 25Ω	--	69.7	--	ns
Turn-on Rise Time	t_r		--	69.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	145	--	
Turn-off Fall Time	t_f		--	59	--	
Drain-Source Body Diode Characteristics						
Body Diode Forward Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 11A, V_{GS} = 0V	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R = 400V, I_F = I_S, di_F/dt = 100A/μs	--	377	--	ns
Reverse Recovery Charge	Q_{rr}		--	3.4	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	17.8	--	A

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_{AS} = 2.4A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. Identical low side and high side switch with identical R_G

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

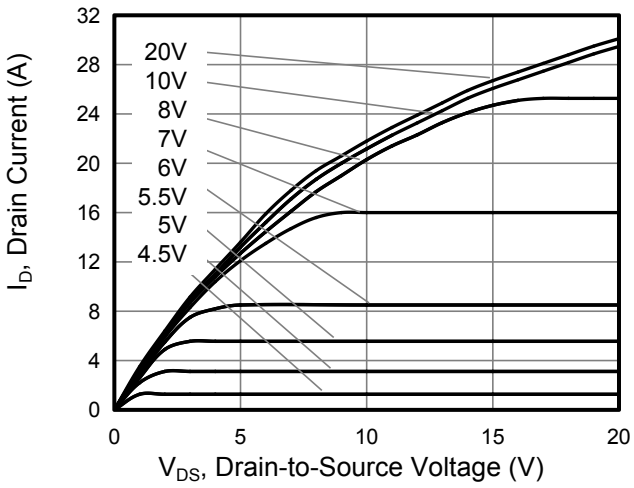


Figure 2. Transfer Characteristics

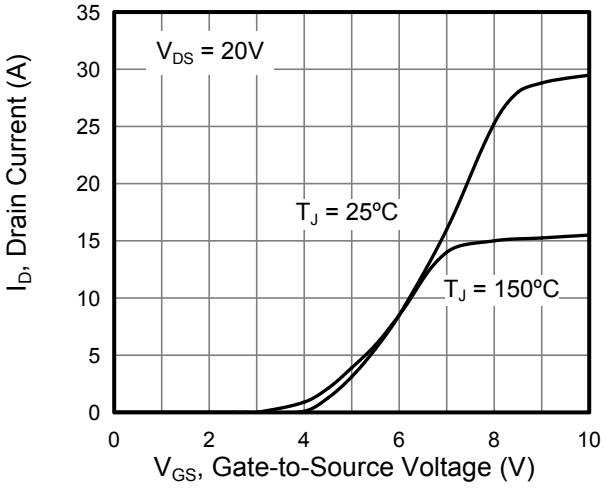


Figure 3. On-Resistance vs. Drain Current

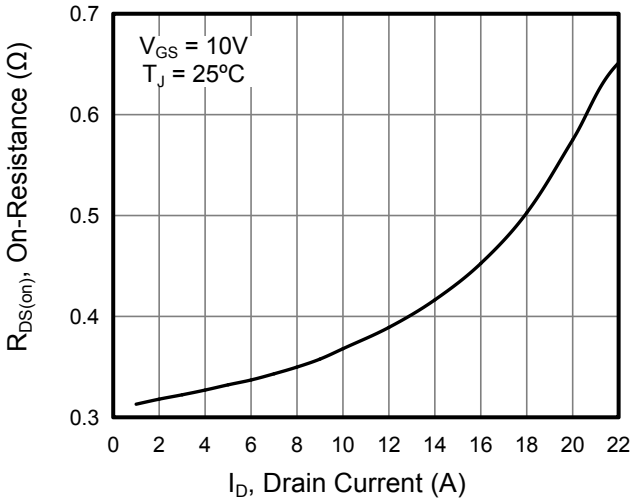


Figure 4. Capacitance

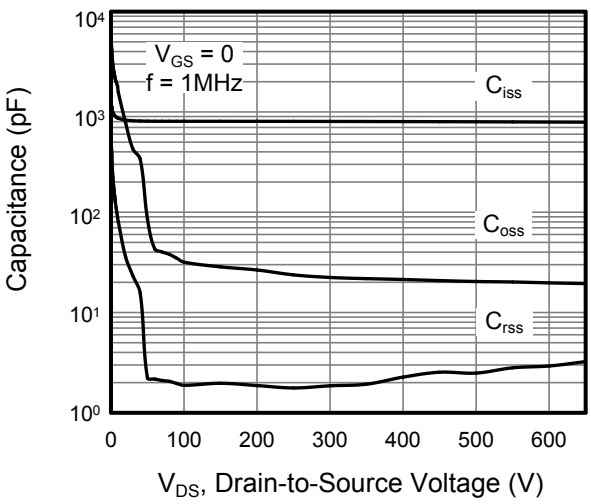


Figure 5. Gate Charge

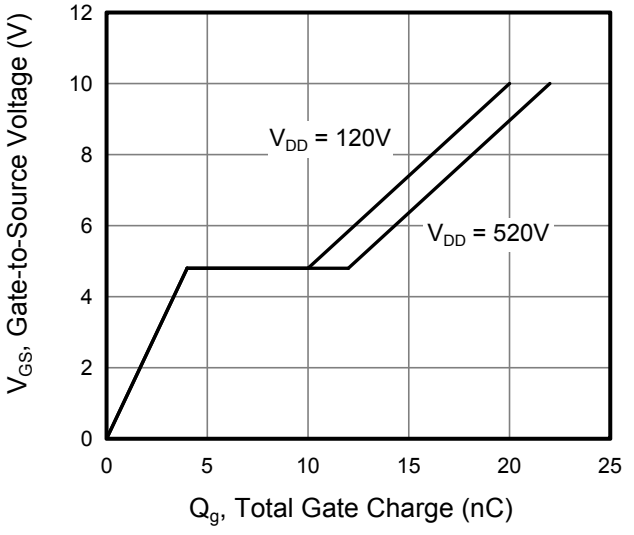
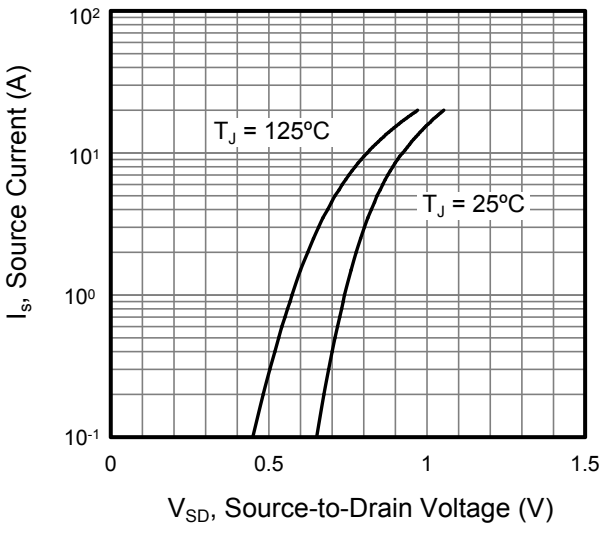


Figure 6. Body Diode Forward Voltage



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. On-Resistance vs. Temperature

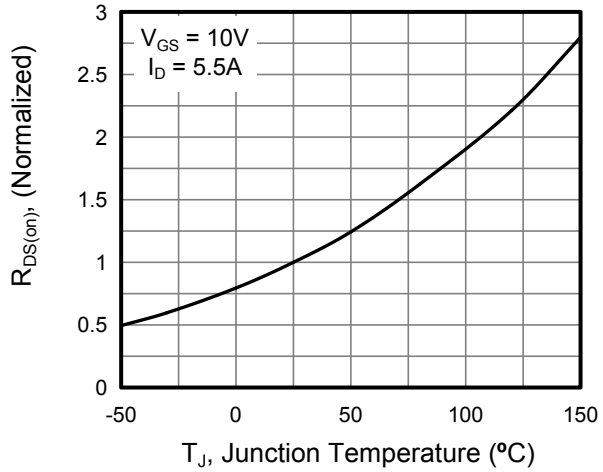


Figure 8.Breakdown Voltage vs. Junction Temperature

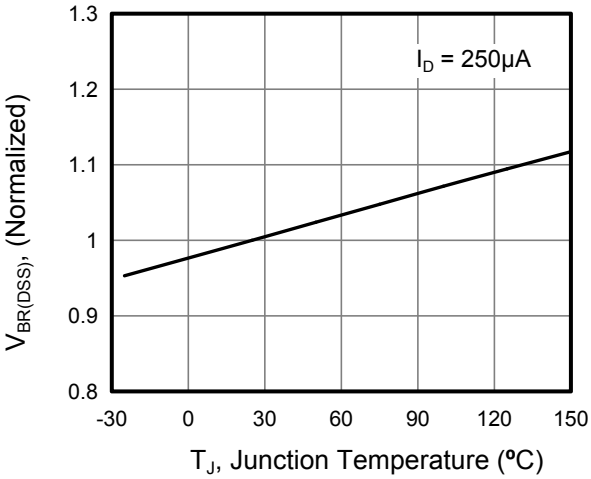


Figure 9. Transient Thermal Impedance For DFN 8*8

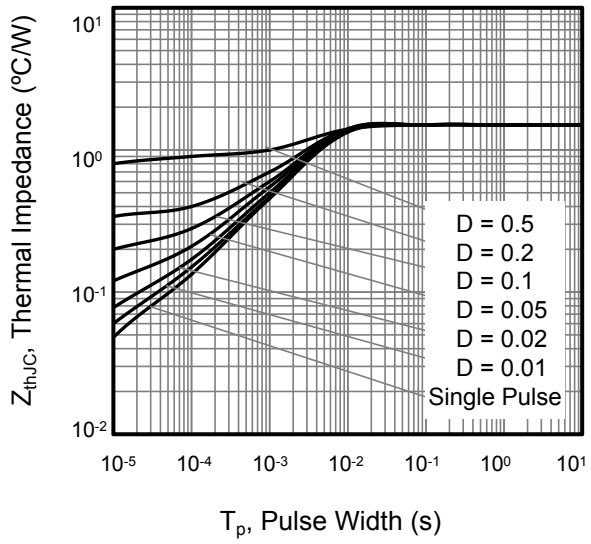


Figure 10. Safe Operation Area For DFN 8*8

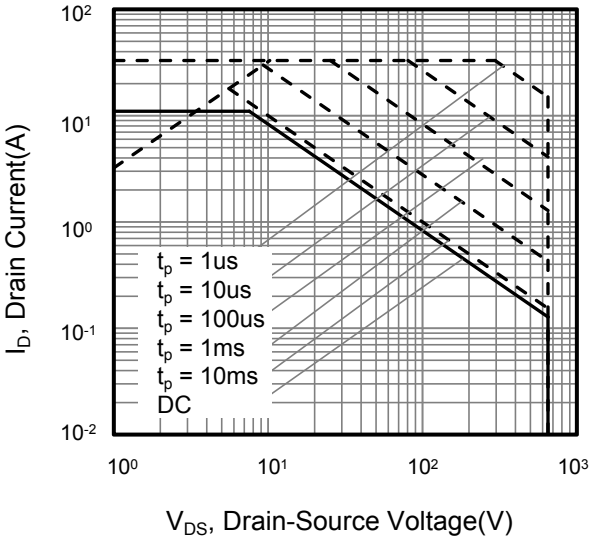


Figure 11. Typ. Coss Stored Energy

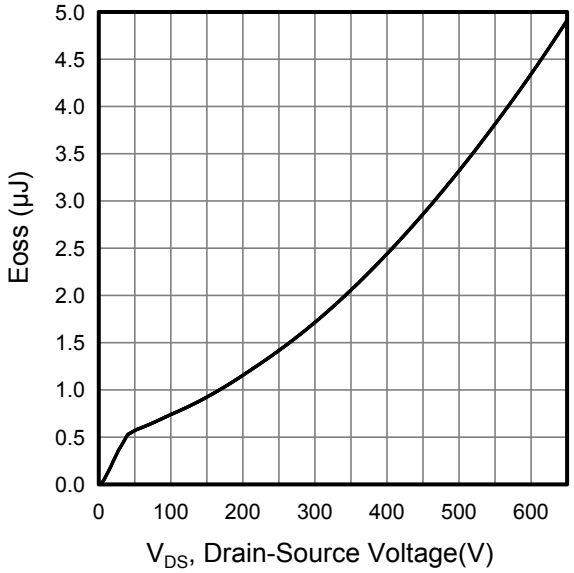


Figure A：Gate Charge Test Circuit and Waveform

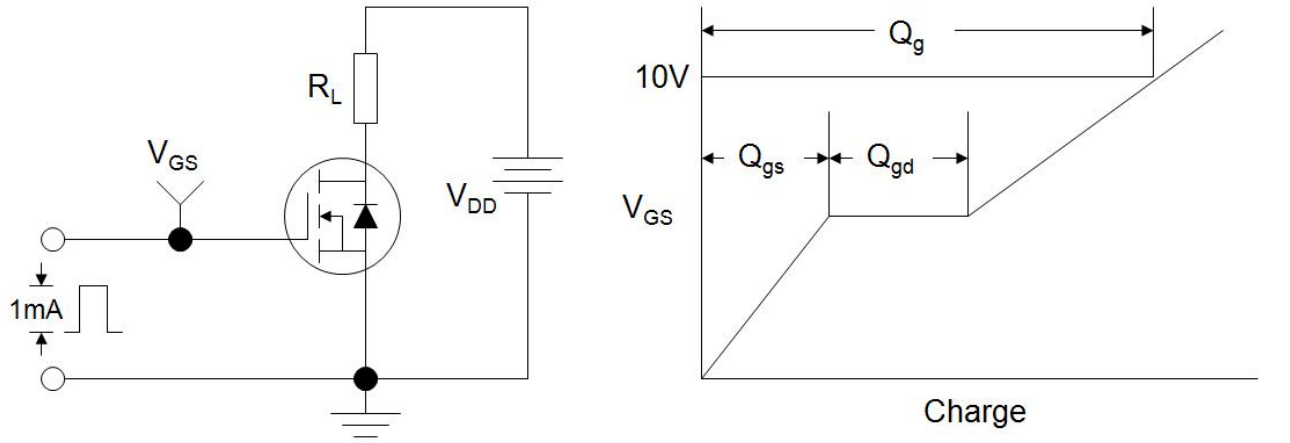


Figure B：Resistive Switching Test Circuit and Waveform

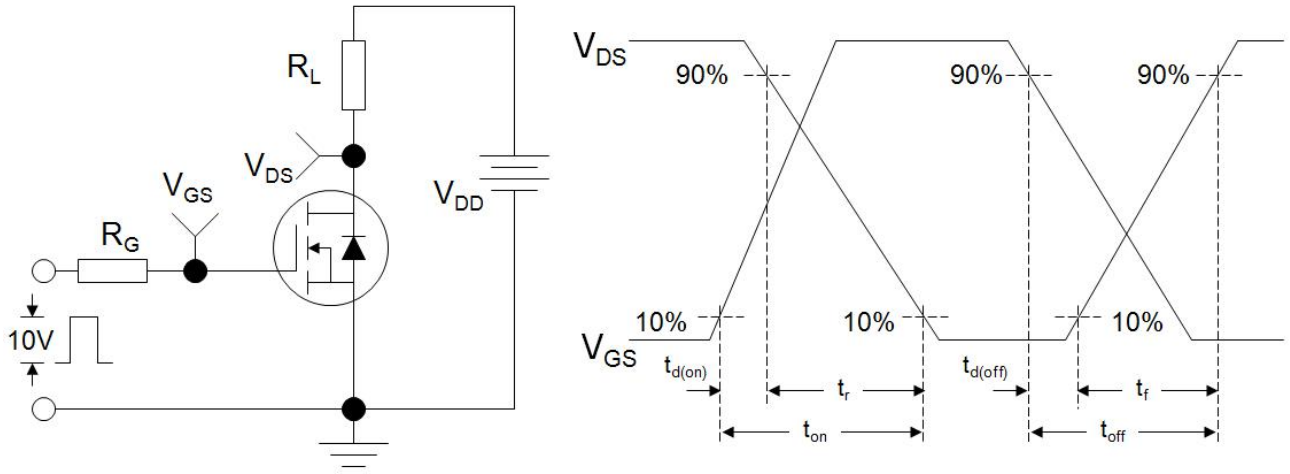
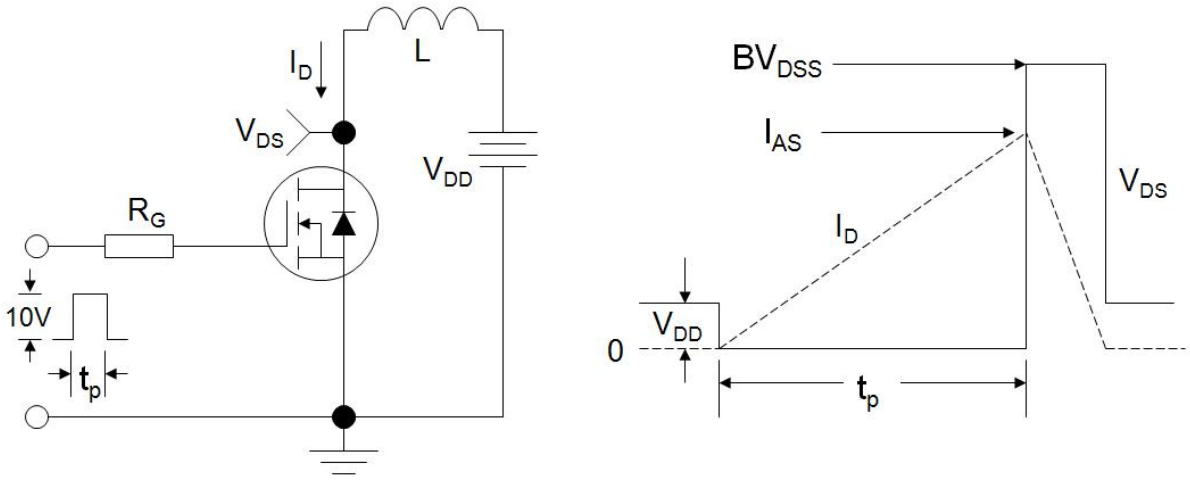
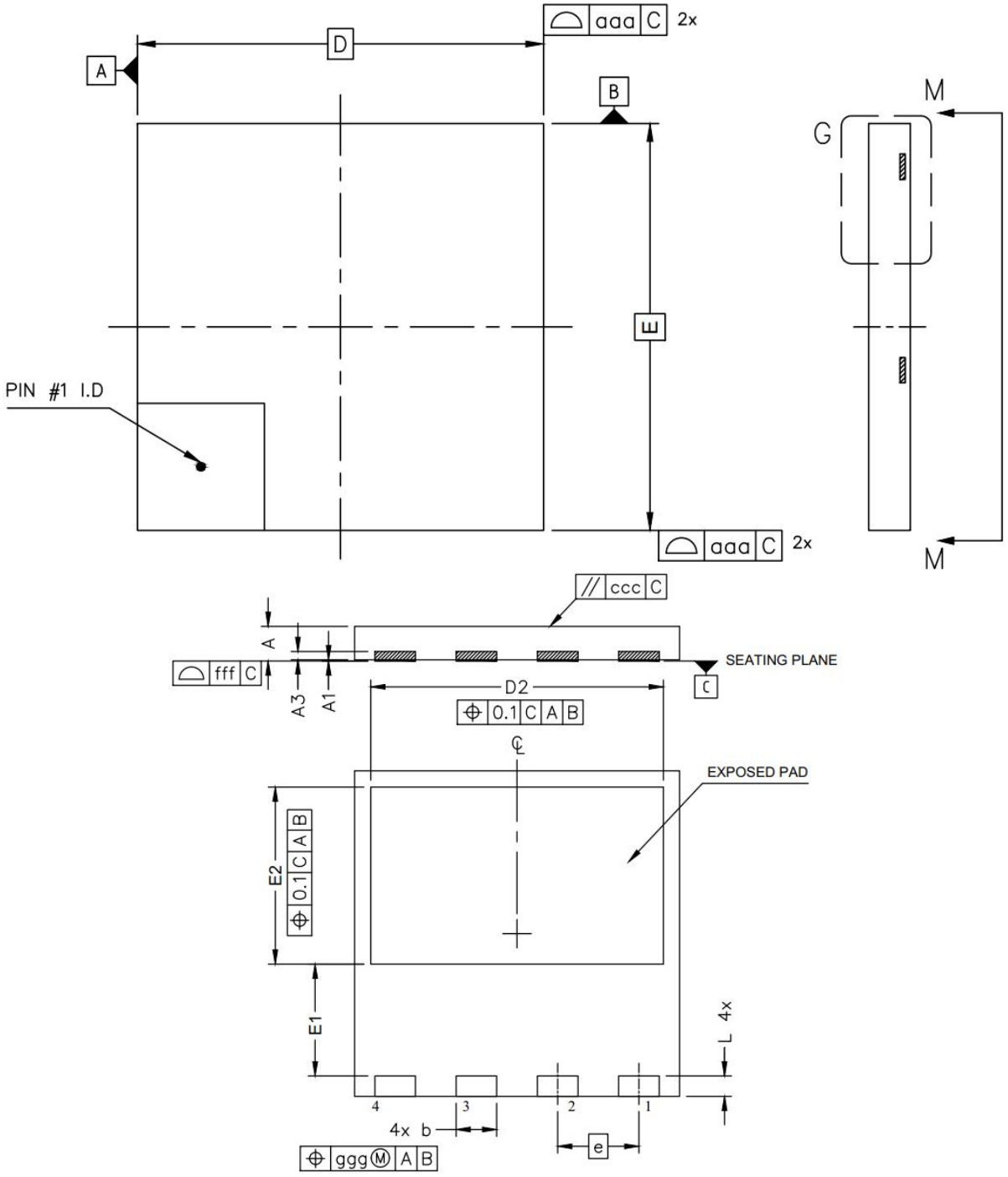


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



DFN 8*8



Unit:mm			
Symbol	**Min.**	**Nom**	**Max.**
A	0.75	0.85	0.95
A1	0.00	-	0.05
A3	0.10	0.20	0.30
b	0.90	1.00	1.10
D	7.90	8.00	8.10
E	7.90	8.00	8.10
D2	7.10	7.20	7.30
E1	2.65	2.75	2.85

Unit:mm			
Symbol	**Min.**	**Nom**	**Max.**
E2	4.25	4.35	4.45
e	2.00 BSC		
L	0.40	0.50	0.60
aaa	0.10		
ggg	0.05		
ccc	0.05		
fff	0.05		

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